

Amendments to the Claims:

This listing of claims will replace all prior version, and listings of claims in the application:

1. (Original) A method for producing a multi-layer device, the method comprising the steps of:
 - providing a substrate comprising a support region for supporting an electrical component in use;
 - forming an electrically conductive bond layer on a surface of the substrate, the bond surrounding the support region;
 - providing an encasing layer in contact with the bond layer, to encase the component between the substrate and the encasing layer; and
 - bonding the encasing layer to the bond layer to form a sealed cavity enclosing the component.
2. (Original) A method according to claim 1, wherein the encasing layer is anodically bonded to the bond layer to form the sealed cavity.
3. (Currently Amended) A method according to claim 1, ~~claims 1 or 2~~, wherein the substrate comprises an electrical conductor, positioned in isolation from the surface provided to receive the bond layer, to connect the component with an external contact pad.
4. (Original) A method according to claim 3, wherein the conductor is formed from at least one conducting layer coupled with conducting plugs.

5. (Original) A method according to claim 4, wherein the conducting layer is surrounded by dielectric layers.

6. (Currently Amended) A method according to claim 1, ~~any preceding claim~~, wherein the component is CMOS or BiCMOS circuitry.

7. (Currently Amended) A method according to claim 1, ~~any of claims 1 to 5~~, wherein the component is a microsensor and/or a micro-actuator.

8. (Currently Amended) A method according to ~~any preceding claim 1~~, further comprising ~~the step of~~ protecting the device from the electric field generated during anodic bonding by placing a conductive shielding layer on the glass wafer and connecting it to the substrate.

9. (Currently Amended) A method according to ~~any preceding claim 1~~, wherein a second encasing layer is bonded to a second surface of the substrate to form a second sealed cavity.

10. (Currently Amended) A method according to ~~any preceding claim 1~~, wherein multiple devices are produced simultaneously on the same substrate, wherein, a bond layer is formed on the surface of the substrate and comprises individual bond members, each of which surrounds a respective component, the bond members being interconnected by plural conducting links to provide an electrical contact path through the bond layer.

11. (Original) A multi-layer device comprising:
- a substrate;
- at least one electrical component located on the substrate;
- an electrically conductive bond layer, formed on the substrate and surrounding the electrical components; and
- an encasing layer, wherein the encasing layer is bonded to the bond layer to form a sealed cavity encasing the components therein.
12. (Original) A device according to claim 11, wherein the encasing layer is anodically bonded to the bond layer to form the sealed cavity.
13. (Currently Amended) A device according to claim 11, ~~claims 11 or 12~~, wherein the substrate comprises an electrical conductor, positioned in isolation from the surface provided to receive the bond layer, to connect the component with an external contact pad.
14. (Original) A device according to claim 13, wherein the conductor is formed from at least one conducting layer coupled with conducting plugs.
15. (Original) A device according to claim 14, wherein the conducting layer is surrounded by dielectric layers.
16. (Currently Amended) A device according to claim 11, ~~any of claims 11 to 15~~,

wherein the component is CMOS or BiCMOS circuitry.

17. (Currently Amended) A device according to claim 11, ~~any of claims 11 to 15~~, wherein the component is a pressure sensor or an inertial sensor.

18. (Currently Amended) A device according to claim 11, ~~any of claims 11 to 17~~, further comprising a conductive shielding layer which is placed on the glass wafer and connected to the substrate, in order to protect the device from ~~the~~ an electric field generated during anodic bonding.

19. (Currently Amended) A device according to claim 11, ~~any of claims 11 to 18~~, wherein a second encasing layer is bonded to a second surface of the substrate to form a second sealed cavity.